## **DESCRIPTION**

The 2SB805-M, 2SB805-L, and 2SB805-K are available in the SOT-89 package.

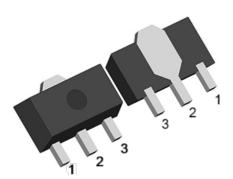
## **FEATURE**

- High collector to emitter voltage: V<sub>CEO</sub>>-100V.
- Excellent h<sub>FE</sub> linearity.

#### **PIN DESCRIPTION**

## ORDERING INFORMATION

| Package Type                             | Part Number   |  |  |
|--|---------------|--|--|
|  | 2SB805-M      |  |  |
| SOT-89                                   | 2SB805-L      |  |  |
|  | 2SB805-K      |  |  |
| SPQ                                      | 1,000pcs/Reel |  |  |
| AiT provides all RoHS Compliant Products |               |  |  |



**SOT-89** 

# **hFE CLASSIFICATION**

| Rank | Range     |  |  |
|------|-----------|--|--|
| M    | 90 ~ 180  |  |  |
| L    | 135 ~ 270 |  |  |
| К    | 200 ~ 400 |  |  |

| PIN# | DESCRIPTION |  |  |
|------|-------------|--|--|
| 1    | Base        |  |  |
| 2    | Collector   |  |  |
| 3    | Emitter     |  |  |

# **ABSOLUTE MAXIMUM RATINGS**

 $T_A = 25$ °C, unless otherwise specified.

| V <sub>CBO</sub> , Collector to Base Voltage           | -100 V        |
|--|---------------|
| V <sub>CEO</sub> , Collector to Emitter Voltage        | -100 V        |
| V <sub>EBO</sub> , Emitter to Base Voltage             | -5 V          |
| Ic, Collector Current-Continuous                       | -0.7 A        |
| I <sub>CM</sub> , Collector Current-Continuous (pulse) | -1.2 A        |
| Pc, Collector Power Dissipation                        | 2000 mW       |
| T <sub>J</sub> , Junction Temperature                  | 150 °C        |
| T <sub>stg</sub> , Storage Temperature                 | -55 ~ +150 °C |

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

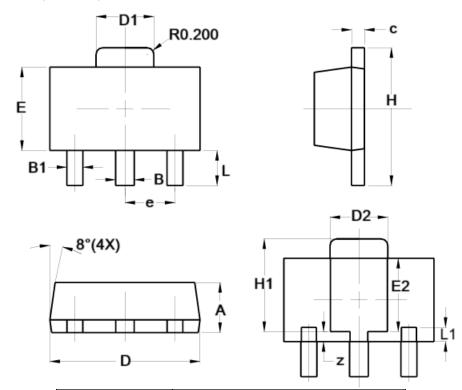
# **ELECTRICAL CHARACTERISTICS**

 $T_A$ =25°C unless otherwise specified.

| Parameter                                       | Symbols               | Conditions                | Min. | Тур. | Max. | Unit |
|---|-----------------------|---------------------------|------|------|------|------|
| Collector Cutoff Current                        | Ісво                  | V <sub>CB</sub> = -100 V, | -    | -    | -100 | nA   |
|   |                       | I <sub>E</sub> = 0        |      |      |      |      |
| Emitter Cutoff Current                          | I <sub>EBO</sub>      | V <sub>EB</sub> = -5 V,   | -    | -    | -100 | nA   |
|   |                       | I <sub>C</sub> = 0        |      |      |      |      |
| DC Current gain                                 | hFE                   | V <sub>CE</sub> = -1 V,   | 90   | 200  | 400  | -    |
|   |                       | I <sub>C</sub> = -100 mA  |      |      |      |      |
|   |                       | V <sub>CE</sub> = -1 V,   | 45   | 200  | -    |      |
|   |                       | I <sub>C</sub> = -5 mA    |      |      |      |      |
| Collector Emitter Saturation Voltage            | V <sub>CE</sub> (sat) | I <sub>C</sub> = -500 mA, | -    | -0.4 | -0.6 | V    |
|   |                       | I <sub>B</sub> = -50 mA,  |      |      |      |      |
| Base Emitter Saturation Voltage V <sub>BE</sub> | V <sub>BE</sub> (sat) | I <sub>C</sub> = -500 mA, | -    | -0.9 | -1.5 | V    |
|   |                       | I <sub>B</sub> = -50 mA,  |      |      |      |      |
| Transition frequency                            | f⊤                    | V <sub>CE</sub> = -10 V,  | -    | 75   | -    | MHz  |
|   |                       | I <sub>E</sub> = 10 mA    |      |      |      |      |
| Output Capacitance                              | Cob                   | V <sub>CB</sub> = -10 V,  | -    | 14   | -    | pF   |
|   |                       | I <sub>E</sub> = 0,       |      |      |      |      |
|   |                       | f = 1 MHz                 |      |      |      |      |

# **PACKAGE INFORMATION**

Dimension in SOT-89 (Unit: mm)



| Complete I | Millimeter |       |  |  |
|------------|------------|-------|--|--|
| Symbol     | Min.       | Max.  |  |  |
| Α          | 1.400      | 1.600 |  |  |
| В          | 0.500      | 0.620 |  |  |
| B1         | 0.420      | 0.540 |  |  |
| С          | 0.350      | 0.430 |  |  |
| D          | 4.440      | 4.600 |  |  |
| D1         | 1.620      | 1.830 |  |  |
| D2         | 1.610      | 1.810 |  |  |
| Е          | 2.400      | 2.600 |  |  |
| E2         | 2.050      | 2.350 |  |  |
| е          | 1.500 TYP. |       |  |  |
| Н          | 3.950      | 4.250 |  |  |
| H1         | 2.630      | 2.930 |  |  |
| L          | 0.900      | 1.200 |  |  |
| L1         | 0.327      | 0.527 |  |  |
| Z          | 0.200      | 0.400 |  |  |

2SB805
TRANSISTOR
SILICON PNP EPITAXIAL PLANAR TRANSISTOR

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- 4 -